

## 7th International Workshop on 2D Materials

**Title of the Presentation:** Electronic structure of multi-layer VTe<sub>2</sub> thin film studied by ARPES

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### Short Biography:

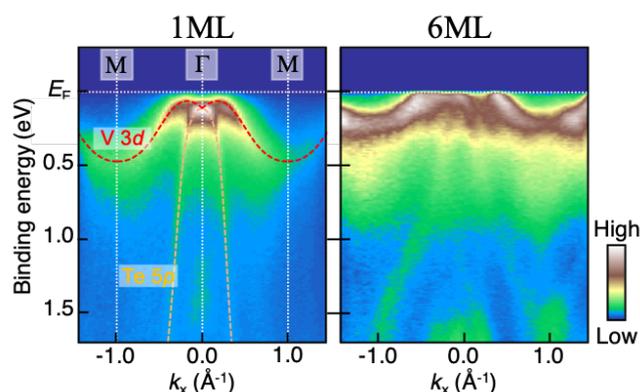
Tappei Kawakami is studying the electronic states of atomically thin transition-metal dichalcogenides by using MBE and high-resolution ARPES. His recent interest is to search for novel physical properties of functional 2D materials.

### Abstract:

The discovery of Dirac electrons in monolayer graphite (graphene) has initiated the search for new functional two-dimensional (2D) materials which exhibit the novel physical properties different from the bulk counterpart. Recently, monolayer transition-metal dichalcogenides (TMDs) are attracting particular attention since they are a promising candidate to explore exotic physical phenomena which are absent in bulk. Amongst TMDs, bulk vanadium ditelluride (VTe<sub>2</sub>) has been reported to exhibit one-dimensional structural phase transition from the octahedral 1T structure to the distorted octahedral 1T'' structure, which is called double-zigzag chain structure at below 482 K [1]. Recently, our group have succeeded in fabricating a monolayer (1ML) VTe<sub>2</sub> thin film on bilayer graphene / SiC by using molecular-beam-epitaxy (MBE) method, and elucidate the electronic structure originated from the 1T structure with angle-resolved photoemission spectroscopy (ARPES) [2]. On the other hands, the origin of different crystal structures between monolayer and bulk has not been understood yet.

To approach this issue, we performed ARPES measurement for multilayer VTe<sub>2</sub> thin film grown by MBE [3]. Figure 1 shows the ARPES results for 1ML (left) and 6ML (right) VTe<sub>2</sub> films along the  $\Gamma M$  direction of first Brillouin zone with 1T structure. For 1ML VTe<sub>2</sub>, one can immediately recognize that the relatively flat band and the dispersive hole-like band exist below the Fermi level ( $E_F$ ), which are assigned as to the V 3d and Te 5p orbitals by comparing with the first-principle calculation, respectively. However, for 6ML VTe<sub>2</sub>, the slightly dispersive flat band corresponding to V3d orbitals apparently crosses  $E_F$ , indicating a metallic nature in 6ML VTe<sub>2</sub>.

In this presentation, we will present the electronic states of multi-layer VTe<sub>2</sub> thin films in more details and discuss the crystal structure transition related with a charge-density wave (CDW) in VTe<sub>2</sub>.



[1] T. Ohtani *et al.*, Solid State Commun. **40**, 629 (1981).

[2] K. Sugawara *et al.*, Phys. Rev. B **99**, 241404(R) (2019).

[3] T. Kawakami *et al.*, submitted.

Fig. 1. ARPES intensity plots for 1ML (left) and 6ML (right) VTe<sub>2</sub> thin films grown on bilayer graphene/SiC. The red and yellow dotted lines represent the V 3d and Te 5p band, respectively.